



SLD8N60U / SLU8N60U 600V N-Channel MOSFET



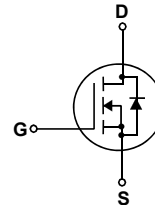
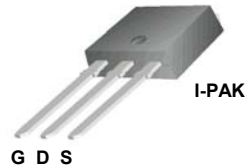
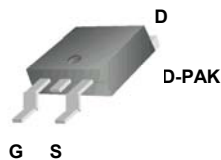
SLD8N60U / SLU8N60U

General Description

This Power MOSFET is produced using Maple semi's advanced planar stripe DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.

Features

- 7.5A, 600V, $R_{DS(on)} = 1.3\Omega @ V_{GS} = 10V$
- Low gate charge (typical 32nC)
- High ruggedness
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	SLD8N60U	SLU8N60U	Units
V_{DSS}	Drain-Source Voltage	600		V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	7.5		A
	- Continuous ($T_C = 100^\circ\text{C}$)	4.6		A
I_{DM}	Drain Current - Pulsed (Note 1)	28		A
V_{GSS}	Gate-Source Voltage	± 30		V
EAS	Single Pulsed Avalanche Energy (Note 2)	350		mJ
I_{AR}	Avalanche Current (Note 1)	7.5		A
E_{AR}	Repetitive Avalanche Energy (Note 1)	15.6		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.0		V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	95		W
	- Derate above 25°C	0.76		W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Max		Units
		SLD8N60U	SLU8N60U	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.32		$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	90		$^\circ\text{C}/\text{W}$

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 uA	600	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 uA, Referenced to 25°C	--	0.59	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600 V, V _{GS} = 0 V	--	--	10	uA
		V _{DS} = 480 V, T _C = 125°C	--	--	100	uA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 uA	2.0	--	4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 3.5A	--	1.0	1.3	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 3.5 A (Note 4)	--	5.6	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	1100	--	pF
C _{oss}	Output Capacitance		--	251	--	pF
C _{rss}	Reverse Transfer Capacitance		--	14	--	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 300 V, I _D =7.5 A, R _G = 25 Ω (Note 4, 5)	--	11	--	ns
t _r	Turn-On Rise Time		--	35	--	ns
t _{d(off)}	Turn-Off Delay Time		--	46	--	ns
t _f	Turn-Off Fall Time		--	40	--	ns
Q _g	Total Gate Charge	V _{DS} = 480 V, I _D = 7.5 A, V _{GS} = 10 V (Note 4, 5)	--	29	--	nC
Q _{gs}	Gate-Source Charge		--	5.5	--	nC
Q _{gd}	Gate-Drain Charge		--	12.5	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	7.5	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	28	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 7.5A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 7.5 A,	--	345	--	ns
Q _{rr}	Reverse Recovery Charge	dl _F / dt = 100 A/us (Note 4)	--	3.2	--	uC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L=11.5\text{ mH}, I_{AS} = 7.5\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\text{ }\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 7.5\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

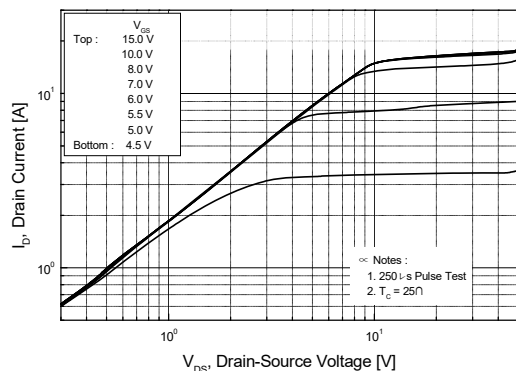


Figure 1. On-Region Characteristics

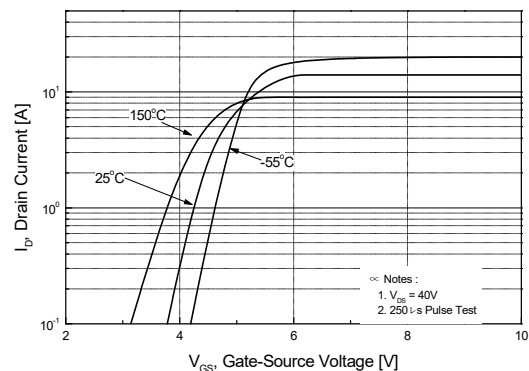


Figure 2. Transfer Characteristics

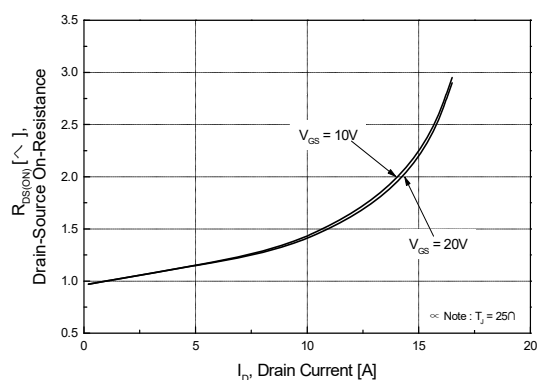


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

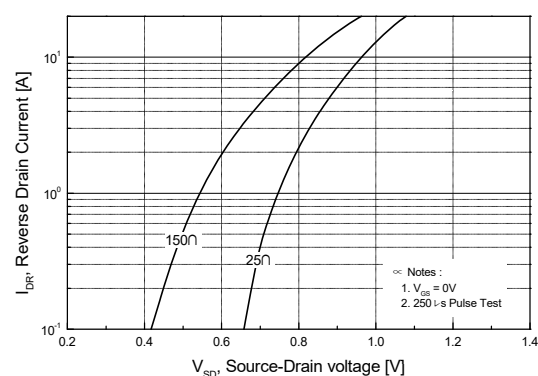


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

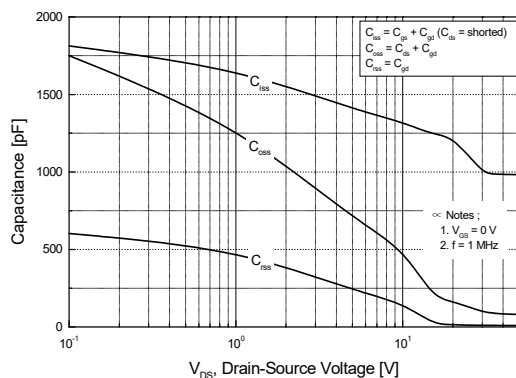


Figure 5. Capacitance Characteristics

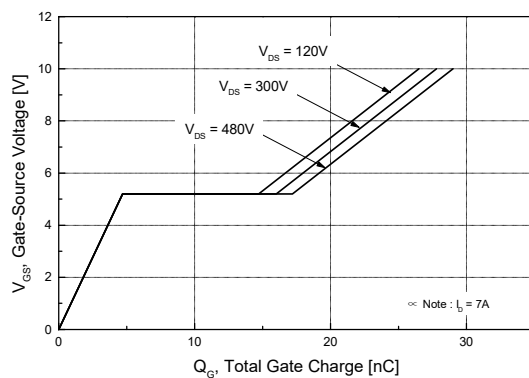


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

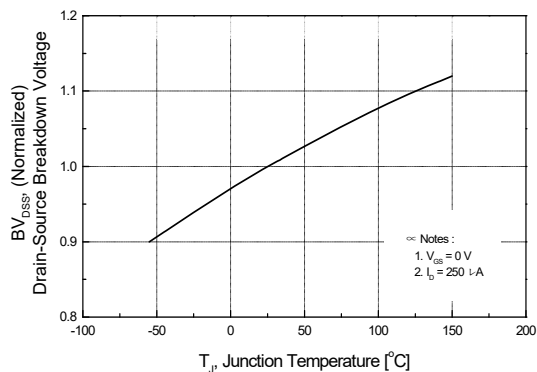


Figure 7. Breakdown Voltage Variation vs Temperature

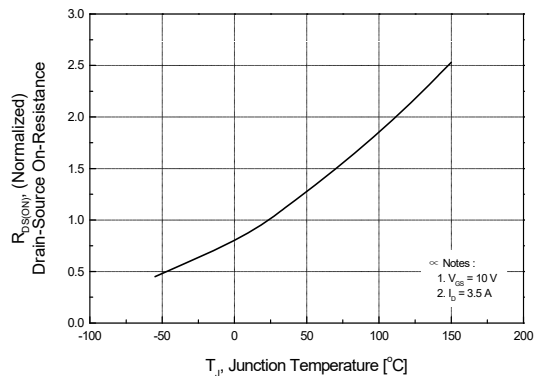


Figure 8. On-Resistance Variation vs Temperature

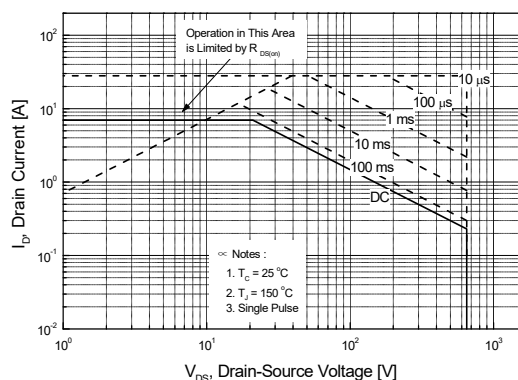


Figure 9. Maximum Safe Operating Area

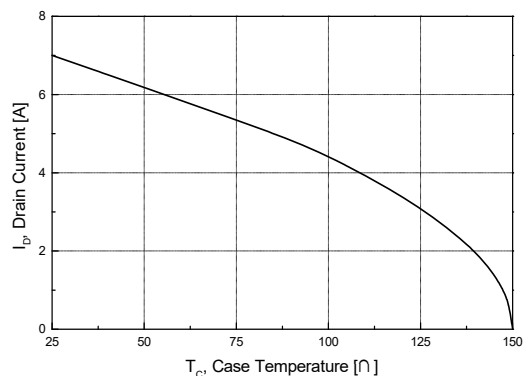


Figure 10. Maximum Drain Current vs Case Temperature

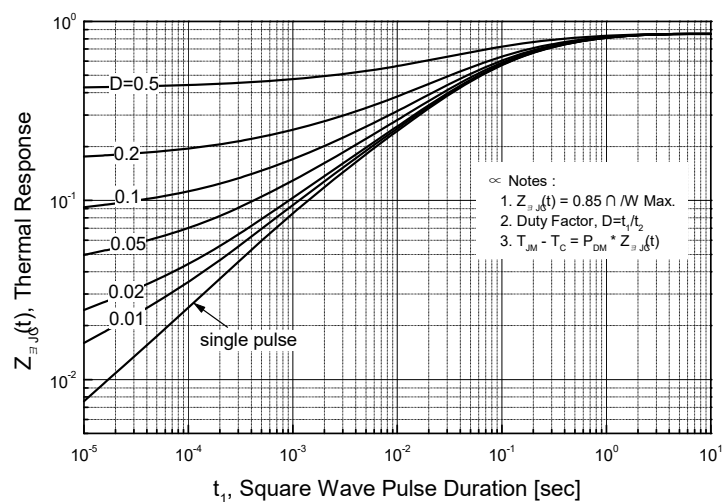
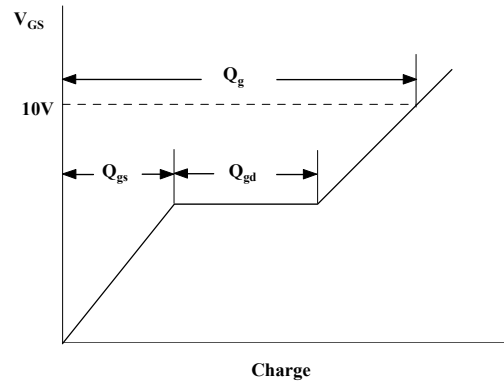
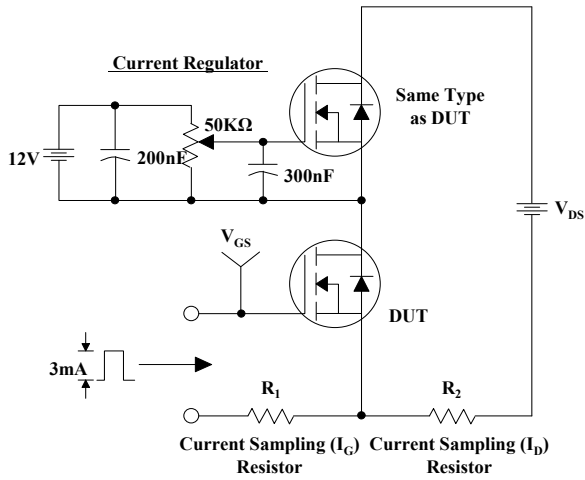
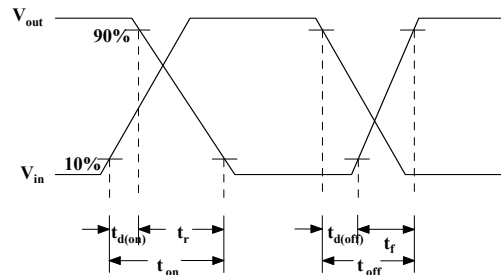
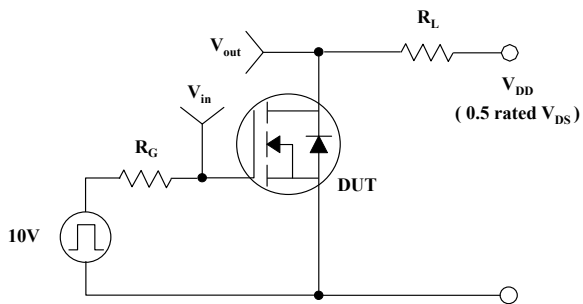


Figure 11. Transient Thermal Response Curve

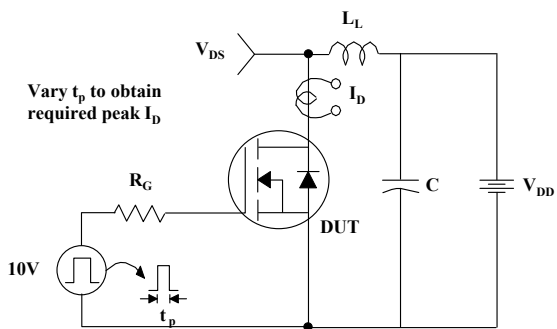
Gate Charge Test Circuit & Waveform



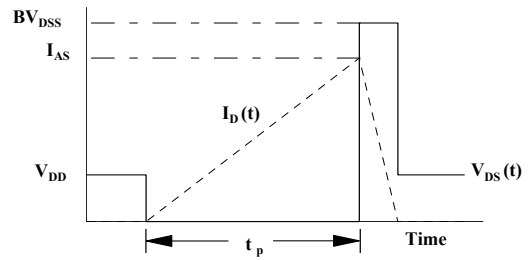
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



$$E_{AS} = \frac{1}{2} L_L I_{AS}^2 - \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



Peak Diode Recovery dv/dt Test Circuit & Waveforms

